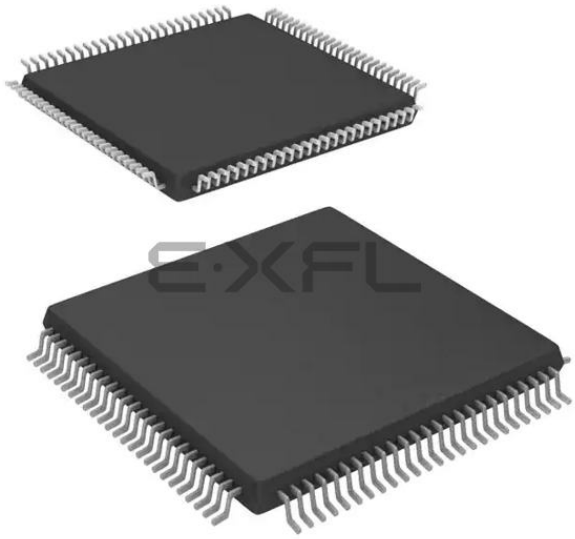

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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	18432
Number of I/O	71
Number of Gates	60000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	100-TQFP
Supplier Device Package	100-VQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a3p060-vq100

I/Os Per Package [1]

ProASIC3 Devices	A3P015[2]	A3P030	A3P060	A3P125	A3P250 [3]		A3P400 [3]		A3P600		A3P1000	
Cortex-M1 Devices					M1A3P250 [3,5]		M1A3P400 [3]		M1A3P600		M1A3P1000	
	I/O Type											
Package	Single-Ended I/O	Single-Ended I/O	Single-Ended I/O	Single-Ended I/O	Single-Ended I/O[4]	Differential I/O Pairs	Single-Ended I/O[4]	Differential I/O Pairs	Single-Ended I/O[4]	Differential I/O Pairs	Single-Ended I/O[4]	Differential I/O Pairs
QN48	–	34	–	–	–	–		–	–	–	–	–
QN68	49	49	–	–	–	–	–	–		–	–	–
QN132[7]	–	81	80	84	87	19	–	–		–	–	–
CS121	–	–	96	–	–	–	–	–	–	–	–	–
VQ100	–	77	71	71	68	13	–	–		–	–	–
TQ144	–	–	91	100	–	–	–	–	–	–	–	–
PQ208	–	–	–	133	151	34	151	34	154	35	154	35
FG144	–	–	96	97	97	24	97	25	97	25	97	25
FG256[5,6]	–	–	–	–	157	38	178	38	177	43	177	44
FG484[6]	–	–	–	–	–	–	194	38	235	60	300	74

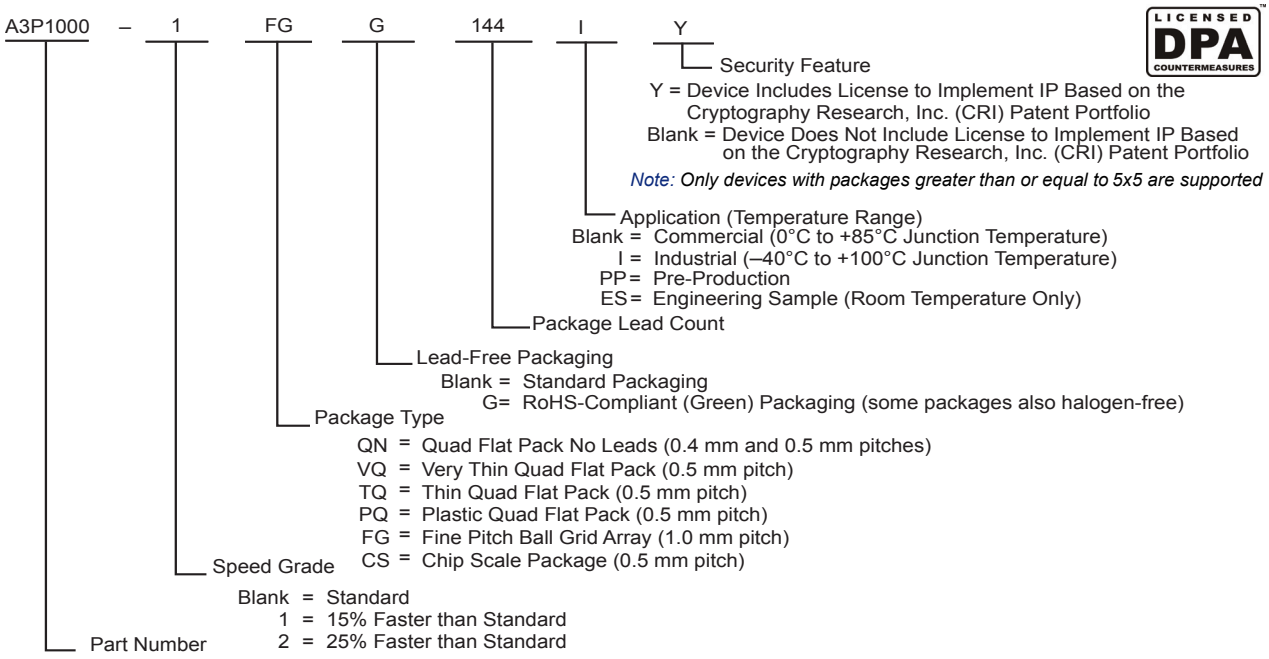
Notes:
1. *When considering migrating your design to a lower- or higher-density device, refer to the ProASIC3 FPGA Fabric User Guide to ensure complying with design and board migration requirements.*
2. *A3P015 is not recommended for new designs.*
3. *For A3P250 and A3P400 devices, the maximum number of LVPECL pairs in east and west banks cannot exceed 15. Refer to the ProASIC3 FPGA Fabric Users Guide for position assignments of the 15 LVPECL pairs.*
4. *Each used differential I/O pair reduces the number of single-ended I/Os available by two.*
5. *The M1A3P250 device does not support FG256 package.*
6. *FG256 and FG484 are footprint-compatible packages.*
7. *Package not available.*

Table 1 • ProASIC3 FPGAs Package Sizes Dimensions

Package	CS121	QN48	QN68	QN132 *	VQ100	TQ144	PQ208	FG144	FG256	FG484
Length × Width (mm × mm)	6 × 6	6 × 6	8 × 8	8 × 8	14 × 14	20 × 20	28 × 28	13 × 13	17 × 17	23 × 23
Nominal Area (mm^2)	36	36	64	64	196	400	784	169	289	529
Pitch (mm)	0.5	0.4	0.4	0.5	0.5	0.5	0.5	1.0	1.0	1.0
Height (mm)	0.99	0.90	0.90	0.75	1.00	1.40	3.40	1.45	1.60	2.23

*Note: * Package not available*

ProASIC3 Ordering Information



ProASIC3 Devices

A3P015 = 15,000 System Gates (A3P015 is not recommended for new designs.)
A3P030 = 30,000 System Gates
A3P060 = 60,000 System Gates
A3P125 = 125,000 System Gates
A3P250 = 250,000 System Gates
A3P400 = 400,000 System Gates
A3P600 = 600,000 System Gates
A3P1000 = 1,000,000 System Gates

ProASIC3 Devices with Cortex-M1

M1A3P250 = 250,000 System Gates
M1A3P400 = 400,000 System Gates
M1A3P600 = 600,000 System Gates
M1A3P1000 = 1,000,000 System Gates

ProASIC3 Device Status

ProASIC3 Devices	Status	Cortex-M1 Devices	Status
A3P015	Not recommended for new designs.		
A3P030	Production		
A3P060	Production		
A3P125	Production		
A3P250	Production	M1A3P250	Production
A3P400	Production	M1A3P400	Production
A3P600	Production	M1A3P600	Production
A3P1000	Production	M1A3P1000	Production

2 – ProASIC3 DC and Switching Characteristics

General Specifications

Operating Conditions

Stresses beyond those listed in Table 2-1 may cause permanent damage to the device.

Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Absolute Maximum Ratings are stress ratings only; functional operation of the device at these or any other conditions beyond those listed under the Recommended Operating Conditions specified in Table 2-2 on page 2-2 is not implied.

Table 2-1 • **Absolute Maximum Ratings**

Symbol	Parameter	Limits	Units
VCC	DC core supply voltage	–0.3 to 1.65	V
VJTAG	JTAG DC voltage	–0.3 to 3.75	V
VPUMP	Programming voltage	–0.3 to 3.75	V
VCCPLL	Analog power supply (PLL)	–0.3 to 1.65	V
VCCI	DC I/O output buffer supply voltage	–0.3 to 3.75	V
VMV	DC I/O input buffer supply voltage	–0.3 to 3.75	V
VI	I/O input voltage	–0.3 V to 3.6 V (when I/O hot insertion mode is enabled) –0.3 V to (VCCI + 1 V) or 3.6 V, whichever voltage is lower (when I/O hot-insertion mode is disabled)	V
T_{STG} [2]	Storage temperature	–65 to +150	°C
T_J [2]	Junction temperature	+125	°C

Notes:

1. *The device should be operated within the limits specified by the datasheet. During transitions, the input signal may undershoot or overshoot according to the limits shown in Table 2-4 on page 2-3.*
2. *VMV pins must be connected to the corresponding VCCI pins. See the "VMVx I/O Supply Voltage (quiet)" section on page 3-1 for further information.*
3. *For flash programming and retention maximum limits, refer to Table 2-3 on page 2-3, and for recommended operating limits, refer to Table 2-2 on page 2-2.*

Power Consumption of Various Internal Resources

Table 2-14 • **Different Components Contributing to Dynamic Power Consumption in ProASIC3 Devices**

Parameter	Definition	Device Specific Dynamic Contributions (µW/MHz)							
		A3P1000	A3P600	A3P400	A3P250	A3P125	A3P060	A3P030	A3P015
PAC1	Clock contribution of a Global Rib	14.50	12.80	12.80	11.00	11.00	9.30	9.30	9.30
PAC2	Clock contribution of a Global Spine	2.48	1.85	1.35	1.58	0.81	0.81	0.41	0.41
PAC3	Clock contribution of a VersaTile row	0.81							
PAC4	Clock contribution of a VersaTile used as a sequential module	0.12							
PAC5	First contribution of a VersaTile used as a sequential module	0.07							
PAC6	Second contribution of a VersaTile used as a sequential module	0.29							
PAC7	Contribution of a VersaTile used as a combinatorial Module	0.29							
PAC8	Average contribution of a routing net	0.70							
PAC9	Contribution of an I/O input pin (standard dependent)	See Table 2-8 on page 2-7 through Table 2-10 on page 2-8.							
PAC10	Contribution of an I/O output pin (standard dependent)	See Table 2-11 on page 2-9 through Table 2-13 on page 2-10.							
PAC11	Average contribution of a RAM block during a read operation	25.00							
PAC12	Average contribution of a RAM block during a write operation	30.00							
PAC13	Dynamic contribution for PLL	2.60							

*Note: *For a different output load, drive strength, or slew rate, Microsemi recommends using the Microsemi Power spreadsheet calculator or SmartPower tool in Libero SoC software.*

Table 2-20 • Summary of Maximum and Minimum DC Input and Output Levels Applicable to Commercial and Industrial Conditions—Software Default Settings Applicable to Standard I/O Banks

I/O Standard	Drive Strength	Equiv. Software Default Drive Strength Option[2]	Slew Rate	VIL		VIH		VOL	VOH	IOL[1] mA	IOH[1] mA
				Min V	Max V	Min V	Max V	Max V	Min V		
3.3 V LVTTL / 3.3 V LVCMOS	8 mA	8 mA	High	–0.3	0.8	2	3.6	0.4	2.4	8	8
3.3 V LVCMOS Wide Range[3]	100 µA	8 mA	High	–0.3	0.8	2	3.6	0.2	VCCI – 0.2	0.1	0.1
2.5 V LVCMOS	8 mA	8 mA	High	–0.3	0.7	1.7	2.7	0.7	1.7	8	8
1.8 V LVCMOS	4 mA	4 mA	High	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.45	VCCI – 0.45	4	4
1.5 V LVCMOS	2 mA	2 mA	High	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	2	2

Notes:

1. *Currents are measured at 85°C junction temperature.*
2. *3.3 V LVCMOS wide range is applicable to 100 µA drive strength only. The configuration will NOT operate at the equivalent software default drive strength. These values are for Normal Ranges ONLY.*
3. *All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD-8B specification.*

Table 2-21 • Summary of Maximum and Minimum DC Input Levels Applicable to Commercial and Industrial Conditions

DC I/O Standards	Commercial[1]		Industrial[2]	
	IIL[3] µA	IIH[4] µA	IIL[3] µA	IIH[4] µA
3.3 V LVTTL / 3.3 V LVCMOS	10	10	15	15
3.3 V LVCMOS Wide Range	10	10	15	15
2.5 V LVCMOS	10	10	15	15
1.8 V LVCMOS	10	10	15	15
1.5 V LVCMOS	10	10	15	15
3.3 V PCI	10	10	15	15
3.3 V PCI-X	10	10	15	15

Notes:

1. *Commercial range (0°C < T_A < 70°C)*
2. *Industrial range (–40°C < T_A < 85°C)*
3. *IIL is the input leakage current per I/O pin over recommended operation conditions where –0.3V < V_{IN} <V_{IL}.*
4. *IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges.*

Single-Ended I/O Characteristics

3.3 V LVTTL / 3.3 V LVCMOS

Low-Voltage Transistor–Transistor Logic (LVTTL) is a general-purpose standard (EIA/JESD) for 3.3 V applications. It uses an LVTTL input buffer and push-pull output buffer.

Table 2-37 • Minimum and Maximum DC Input and Output Levels Applicable to Advanced I/O Banks

3.3 V LVTTL / 3.3 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL[1]	IIH[2]
Drive Strength	Min V	Max V	Min V	Max V	Max V	Min V	mA	mA	Max mA[3]	Max mA[3]	µA[4]	µA[4]
2 mA	–0.3	0.8	2	3.6	0.4	2.4	2	2	27	25	10	10
4 mA	–0.3	0.8	2	3.6	0.4	2.4	4	4	27	25	10	10
6 mA	–0.3	0.8	2	3.6	0.4	2.4	6	6	54	51	10	10
8 mA	–0.3	0.8	2	3.6	0.4	2.4	8	8	54	51	10	10
12 mA	–0.3	0.8	2	3.6	0.4	2.4	12	12	109	103	10	10
16 mA	–0.3	0.8	2	3.6	0.4	2.4	16	16	127	132	10	10
24 mA	–0.3	0.8	2	3.6	0.4	2.4	24	24	181	268	10	10

Notes:

1. *IIL is the input leakage current per I/O pin over recommended operation conditions where –0.3 V < VIN < VIL.*
2. *IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges*
3. *Currents are measured at 100°C junction temperature and maximum voltage.*
4. *Currents are measured at 85°C junction temperature.*
5. *Software default selection highlighted in gray.*

Table 2-38 • Minimum and Maximum DC Input and Output Levels Applicable to Standard Plus I/O Banks

3.3 V LVTTL / 3.3 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL[1]	IIH[2]
Drive Strength	Min V	Max V	Min V	Max V	Max V	Min V	mA	mA	Max mA[3]	Max mA[3]	µA[4]	µA[4]
2 mA	–0.3	0.8	2	3.6	0.4	2.4	2	2	27	25	10	10
4 mA	–0.3	0.8	2	3.6	0.4	2.4	4	4	27	25	10	10
6 mA	–0.3	0.8	2	3.6	0.4	2.4	6	6	54	51	10	10
8 mA	–0.3	0.8	2	3.6	0.4	2.4	8	8	54	51	10	10
12 mA	–0.3	0.8	2	3.6	0.4	2.4	12	12	109	103	10	10
16 mA	–0.3	0.8	2	3.6	0.4	2.4	16	16	109	103	10	10

Notes:

1. *IIL is the input leakage current per I/O pin over recommended operation conditions where –0.3 V < VIN < VIL.*
2. *IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges*
3. *Currents are measured at 100°C junction temperature and maximum voltage.*
4. *Currents are measured at 85°C junction temperature.*
5. *Software default selection highlighted in gray.*

Table 2-43 • 3.3 V LVTTL / 3.3 V LVCMOS High Slew
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V
Applicable to Standard Plus I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.66	7.20	0.04	1.00	0.43	7.34	6.29	2.27	2.34	9.57	8.52	ns
	–1	0.56	6.13	0.04	0.85	0.36	6.24	5.35	1.93	1.99	8.14	7.25	ns
	–2	0.49	5.38	0.03	0.75	0.32	5.48	4.69	1.70	1.75	7.15	6.36	ns
4 mA	Std.	0.66	7.20	0.04	1.00	0.43	7.34	6.29	2.27	2.34	9.57	8.52	ns
	–1	0.56	6.13	0.04	0.85	0.36	6.24	5.35	1.93	1.99	8.14	7.25	ns
	–2	0.49	5.38	0.03	0.75	0.32	5.48	4.69	1.70	1.75	7.15	6.36	ns
6 mA	Std.	0.66	4.50	0.04	1.00	0.43	4.58	3.82	2.58	2.88	6.82	6.05	ns
	–1	0.56	3.83	0.04	0.85	0.36	3.90	3.25	2.19	2.45	5.80	5.15	ns
	–2	0.49	3.36	0.03	0.75	0.32	3.42	2.85	1.92	2.15	5.09	4.52	ns
8 mA	Std.	0.66	4.50	0.04	1.00	0.43	4.58	3.82	2.58	2.88	6.82	6.05	ns
	–1	0.56	3.83	0.04	0.85	0.36	3.90	3.25	2.19	2.45	5.80	5.15	ns
	–2	0.49	3.36	0.03	0.75	0.32	3.42	2.85	1.92	2.15	5.09	4.52	ns
12 mA	Std.	0.66	3.16	0.04	1.00	0.43	3.22	2.58	2.79	3.22	5.45	4.82	ns
	–1	0.56	2.69	0.04	0.85	0.36	2.74	2.20	2.37	2.74	4.64	4.10	ns
	–2	0.49	2.36	0.03	0.75	0.32	2.40	1.93	2.08	2.41	4.07	3.60	ns
16 mA	Std.	0.66	3.16	0.04	1.00	0.43	3.22	2.58	2.79	3.22	5.45	4.82	ns
	–1	0.56	2.69	0.04	0.85	0.36	2.74	2.20	2.37	2.74	4.64	4.10	ns
	–2	0.49	2.36	0.03	0.75	0.32	2.40	1.93	2.08	2.41	4.07	3.60	ns

Notes:

1. *Software default selection highlighted in gray.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

Table 2-81 • 1.5 V LVCMOS Low Slew
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.4 V
Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.66	12.78	0.04	1.44	0.43	12.81	12.78	3.40	2.64	15.05	15.02	ns
	–1	0.56	10.87	0.04	1.22	0.36	10.90	10.87	2.89	2.25	12.80	12.78	ns
	–2	0.49	9.55	0.03	1.07	0.32	9.57	9.55	2.54	1.97	11.24	11.22	ns
4 mA	Std.	0.66	10.01	0.04	1.44	0.43	10.19	9.55	3.75	3.27	12.43	11.78	ns
	–1	0.56	8.51	0.04	1.22	0.36	8.67	8.12	3.19	2.78	10.57	10.02	ns
	–2	0.49	7.47	0.03	1.07	0.32	7.61	7.13	2.80	2.44	9.28	8.80	ns
6 mA	Std.	0.66	9.33	0.04	1.44	0.43	9.51	8.89	3.83	3.43	11.74	11.13	ns
	–1	0.56	7.94	0.04	1.22	0.36	8.09	7.56	3.26	2.92	9.99	9.47	ns
	–2	0.49	6.97	0.03	1.07	0.32	7.10	6.64	2.86	2.56	8.77	8.31	ns
8 mA	Std.	0.66	8.91	0.04	1.44	0.43	9.07	8.89	3.95	4.05	11.31	11.13	ns
	–1	0.56	7.58	0.04	1.22	0.36	7.72	7.57	3.36	3.44	9.62	9.47	ns
	–2	0.49	6.65	0.03	1.07	0.32	6.78	6.64	2.95	3.02	8.45	8.31	ns
12 mA	Std.	0.66	8.91	0.04	1.44	0.43	9.07	8.89	3.95	4.05	11.31	11.13	ns
	–1	0.56	7.58	0.04	1.22	0.36	7.72	7.57	3.36	3.44	9.62	9.47	ns
	–2	0.49	6.65	0.03	1.07	0.32	6.78	6.64	2.95	3.02	8.45	8.31	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

Table 2-82 • 1.5 V LVCMOS High Slew
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.4 V
Applicable to Standard Plus I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.66	7.83	0.04	1.42	0.43	6.42	7.83	2.71	2.55	8.65	10.07	ns
	–1	0.56	6.66	0.04	1.21	0.36	5.46	6.66	2.31	2.17	7.36	8.56	ns
	–2	0.49	5.85	0.03	1.06	0.32	4.79	5.85	2.02	1.90	6.46	7.52	ns
4 mA	Std.	0.66	4.84	0.04	1.42	0.43	4.49	4.84	3.03	3.13	6.72	7.08	ns
	–1	0.56	4.12	0.04	1.21	0.36	3.82	4.12	2.58	2.66	5.72	6.02	ns
	–2	0.49	3.61	0.03	1.06	0.32	3.35	3.61	2.26	2.34	5.02	5.28	ns

Notes:

1. *Software default selection highlighted in gray.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

Output DDR Module

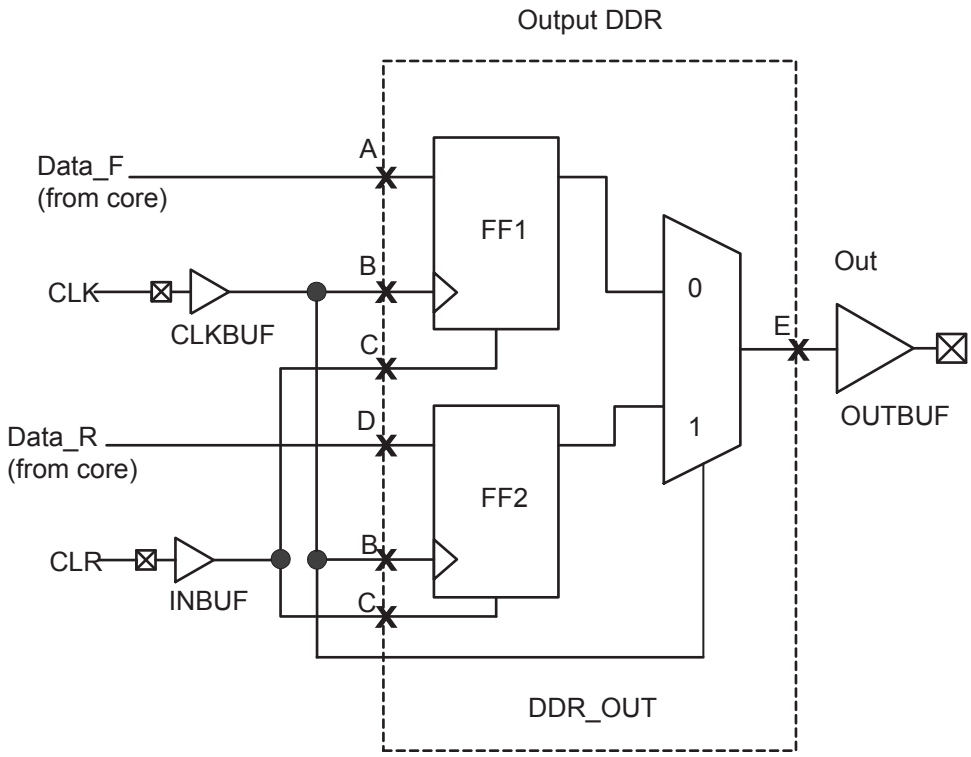


Figure 2-22 • **Output DDR Timing Model**

Table 2-103 • **Parameter Definitions**

Parameter Name	Parameter Definition	Measuring Nodes (from, to)
$t_{DDROCLKQ}$	Clock-to-Out	B, E
$t_{DDROCLR2Q}$	Asynchronous Clear-to-Out	C, E
$t_{DDROREMCLR}$	Clear Removal	C, B
$t_{DDRORECCLR}$	Clear Recovery	C, B
$t_{DDROSUD1}$	Data Setup Data_F	A, B
$t_{DDROSUD2}$	Data Setup Data_R	D, B
$t_{DDROHD1}$	Data Hold Data_F	A, B
$t_{DDROHD2}$	Data Hold Data_R	D, B

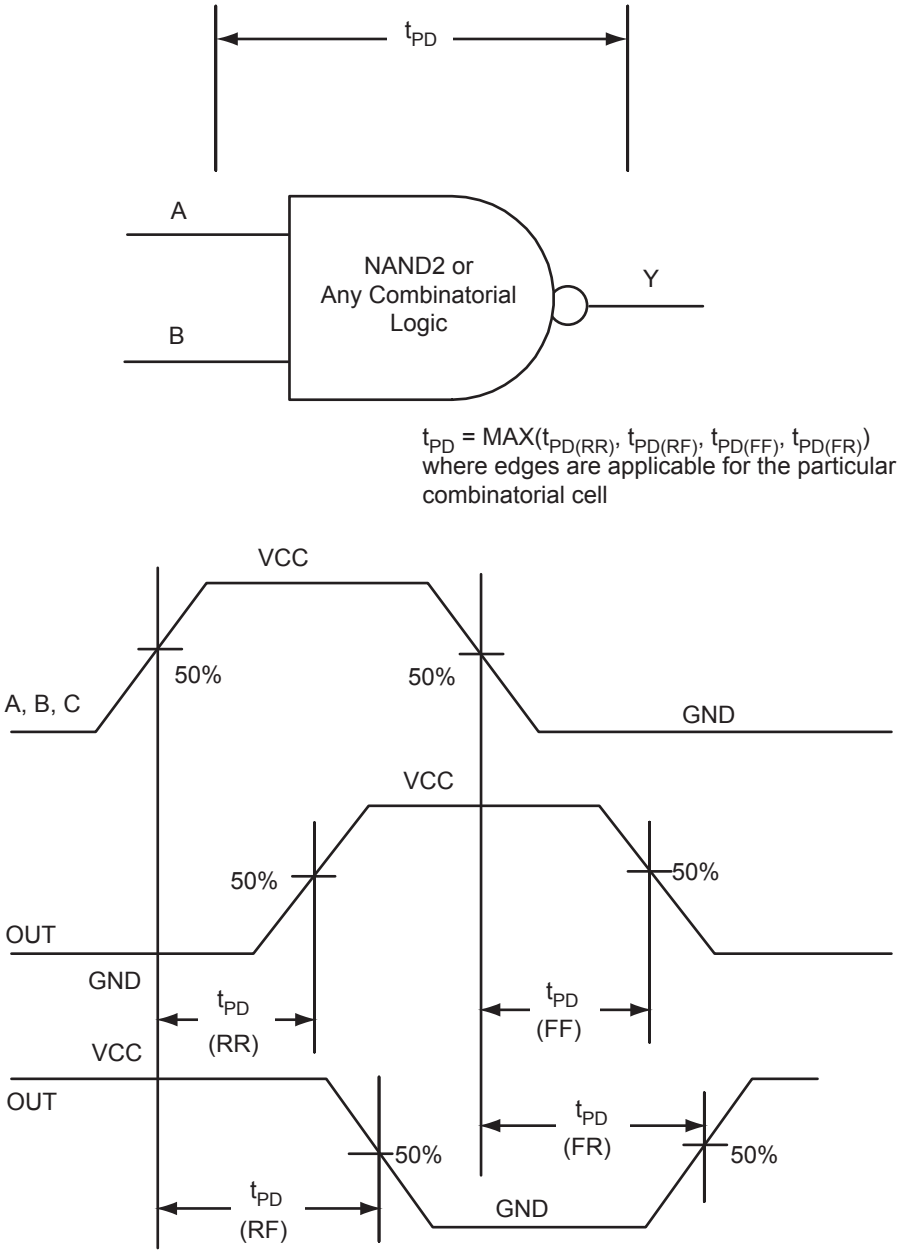


Figure 2-25 • **Timing Model and Waveforms**

Global Resource Characteristics

A3P250 Clock Tree Topology

Clock delays are device-specific. Figure 2-28 is an example of a global tree used for clock routing. The global tree presented in Figure 2-28 is driven by a CCC located on the west side of the A3P250 device. It is used to drive all D-flip-flops in the device.

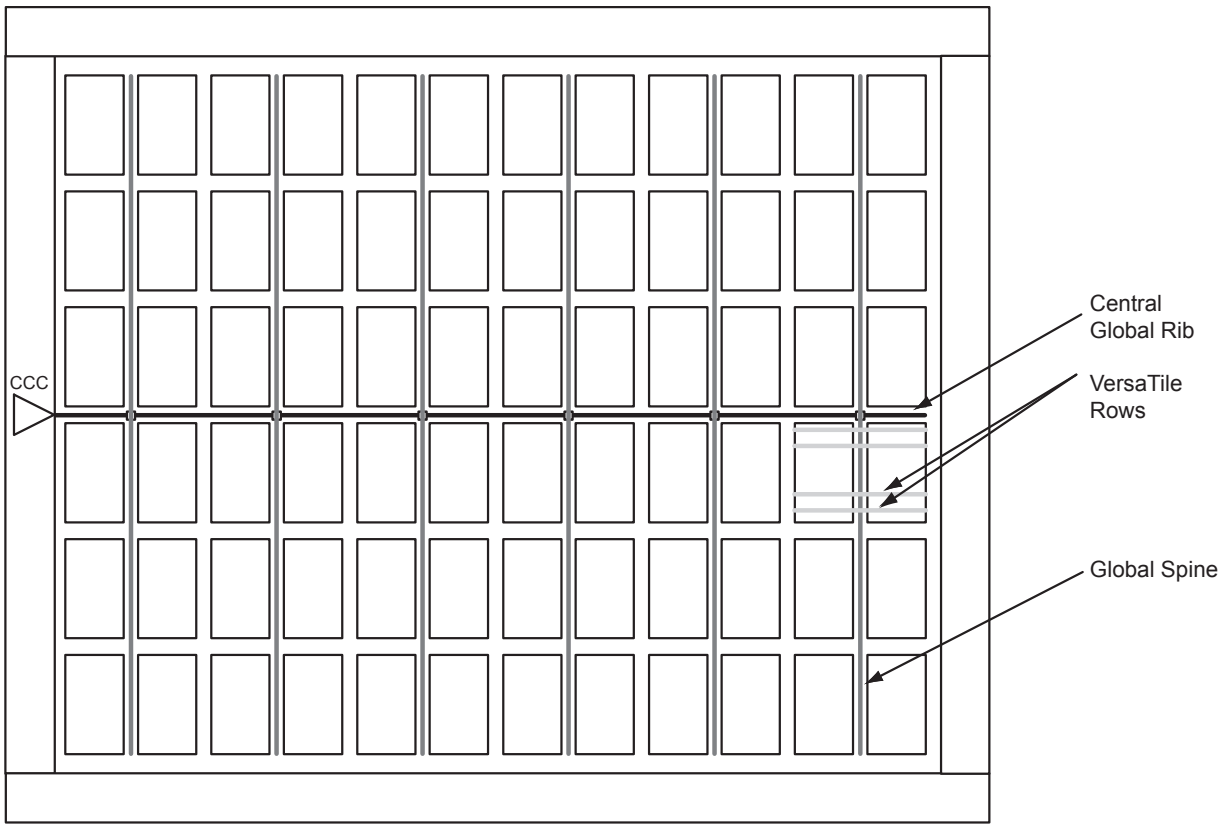


Figure 2-28 • **Example of Global Tree Use in an A3P250 Device for Clock Routing**

Global Tree Timing Characteristics

Global clock delays include the central rib delay, the spine delay, and the row delay. Delays do not include I/O input buffer clock delays, as these are I/O standard–dependent, and the clock may be driven and conditioned internally by the CCC module. For more details on clock conditioning capabilities, refer to the "Clock Conditioning Circuits" section on page 2-90. Table 2-108 to Table 2-114 on page 2-89 present minimum and maximum global clock delays within each device. Minimum and maximum delays are measured with minimum and maximum loading.

Table 2-117 • RAM512X18
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V

Parameter	Description	–2	–1	Std.	Units
t_{AS}	Address setup time	0.25	0.28	0.33	ns
t_{AH}	Address hold time	0.00	0.00	0.00	ns
t_{ENS}	REN, WEN setup time	0.13	0.15	0.17	ns
t_{ENH}	REN, WEN hold time	0.10	0.11	0.13	ns
t_{DS}	Input data (WD) setup time	0.18	0.21	0.25	ns
t_{DH}	Input data (WD) hold time	0.00	0.00	0.00	ns
t_{CKQ1}	Clock High to new data valid on RD (output retained)	2.16	2.46	2.89	ns
t_{CKQ2}	Clock High to new data valid on RD (pipelined)	0.90	1.02	1.20	ns
t_{C2CRWH}[1]	Address collision clk-to-clk delay for reliable read access after write on same address—Applicable to Opening Edge	0.50	0.43	0.38	ns
t_{C2CWRH}[1]	Address collision clk-to-clk delay for reliable write access after read on same address—Applicable to Opening Edge	0.59	0.50	0.44	ns
t_{RSTBQ}	RESET Low to data out Low on RD (flow-through)	0.92	1.05	1.23	ns
	RESET Low to data out Low on RD (pipelined)	0.92	1.05	1.23	ns
$t_{REMRSTB}$	RESET removal	0.29	0.33	0.38	ns
$t_{RECRSTB}$	RESET recovery	1.50	1.71	2.01	ns
$t_{MPWRSTB}$	RESET minimum pulse width	0.21	0.24	0.29	ns
t_{CYC}	Clock cycle time	3.23	3.68	4.32	ns
F_{MAX}	Maximum frequency	310	272	231	MHz

Notes:

1. *For more information, refer to the application note Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

mode is not used in the design, the FF pin is available as a regular I/O. For IGLOOe, ProASIC3EL, and RT ProASIC3 only, the FF pin can be configured as a Schmitt trigger input.

When Flash*Freeze mode is used, the FF pin must not be left floating to avoid accidentally entering Flash*Freeze mode. While in Flash*Freeze mode, the Flash*Freeze pin should be constantly asserted.

The Flash*Freeze pin can be used with any single-ended I/O standard supported by the I/O bank in which the pin is located, and input signal levels compatible with the I/O standard selected. The FF pin should be treated as a sensitive asynchronous signal. When defining pin placement and board layout, simultaneously switching outputs (SSOs) and their effects on sensitive asynchronous pins must be considered.

Unused FF or I/O pins are tristated with weak pull-up. This default configuration applies to both Flash*Freeze mode and normal operation mode. No user intervention is required.

JTAG Pins

Low power flash devices have a separate bank for the dedicated JTAG pins. The JTAG pins can be run at any voltage from 1.5 V to 3.3 V (nominal). VCC must also be powered for the JTAG state machine to operate, even if the device is in bypass mode; VJTAG alone is insufficient. Both VJTAG and VCC to the part must be supplied to allow JTAG signals to transition the device. Isolating the JTAG power supply in a separate I/O bank gives greater flexibility in supply selection and simplifies power supply and PCB design. If the JTAG interface is neither used nor planned for use, the VJTAG pin together with the TRST pin could be tied to GND.

TCK Test Clock

Test clock input for JTAG boundary scan, ISP, and UJTAG. The TCK pin does not have an internal pull-up/-down resistor. If JTAG is not used, Microsemi recommends tying off TCK to GND through a resistor placed close to the FPGA pin. This prevents JTAG operation in case TMS enters an undesired state.

Note that to operate at all VJTAG voltages, 500 Ω to 1 kΩ will satisfy the requirements. Refer to Table 1 for more information.

Table 1 • **Recommended Tie-Off Values for the TCK and TRST Pins**

VJTAG	Tie-Off Resistance
3.3 V	200 Ω –1 kΩ
2.5 V	200 Ω –1 kΩ
1.8 V	500 Ω –1 kΩ
1.5 V	500 Ω –1 kΩ

Notes:

1. *Equivalent parallel resistance if more than one device is on the JTAG chain*
2. *The TCK pin can be pulled up/down.*
3. *The TRST pin is pulled down.*

TDI Test Data Input

Serial input for JTAG boundary scan, ISP, and UJTAG usage. There is an internal weak pull-up resistor on the TDI pin.

TDO Test Data Output

Serial output for JTAG boundary scan, ISP, and UJTAG usage.

TMS Test Mode Select

The TMS pin controls the use of the IEEE 1532 boundary scan pins (TCK, TDI, TDO, TRST). There is an internal weak pull-up resistor on the TMS pin.

TRST Boundary Scan Reset Pin

The TRST pin functions as an active low input to asynchronously initialize (or reset) the boundary scan circuitry. There is an internal weak pull-up resistor on the TRST pin. If JTAG is not used, an external pull-down resistor could be included to ensure the test access port (TAP) is held in reset mode. The resistor values must be chosen from Table 1 and must satisfy the parallel resistance value requirement. The values in Table 1 correspond to the resistor recommended when a single device is used, and the equivalent parallel resistor when multiple devices are connected via a JTAG chain.

QN132	
Pin Number	**A3P030 Function**
C17	IO51RSB1
C18	NC
C19	TCK
C20	NC
C21	VPUMP
C22	VJTAG
C23	NC
C24	NC
C25	NC
C26	GDB0/IO38RSB0
C27	NC
C28	VCCIB0
C29	IO32RSB0
C30	IO29RSB0
C31	IO28RSB0
C32	IO25RSB0
C33	NC
C34	NC
C35	VCCIB0
C36	IO17RSB0
C37	IO14RSB0
C38	IO11RSB0
C39	IO07RSB0
C40	IO04RSB0
D1	GND
D2	GND
D3	GND
D4	GND

TQ144	
Pin Number	**A3P125 Function**
109	GBA1/IO40RSB0
110	GBA0/IO39RSB0
111	GBB1/IO38RSB0
112	GBB0/IO37RSB0
113	GBC1/IO36RSB0
114	GBC0/IO35RSB0
115	IO34RSB0
116	IO33RSB0
117	VCCIB0
118	GND
119	VCC
120	IO29RSB0
121	IO28RSB0
122	IO27RSB0
123	IO25RSB0
124	IO23RSB0
125	IO21RSB0
126	IO19RSB0
127	IO17RSB0
128	IO16RSB0
129	IO14RSB0
130	IO12RSB0
131	IO10RSB0
132	IO08RSB0
133	IO06RSB0
134	VCCIB0
135	GND
136	VCC
137	GAC1/IO05RSB0
138	GAC0/IO04RSB0
139	GAB1/IO03RSB0
140	GAB0/IO02RSB0
141	GAA1/IO01RSB0
142	GAA0/IO00RSB0
143	GNDQ
144	VMV0

FG144	
Pin Number	**A3P125 Function**
K1	GEB0/IO109RSB1
K2	GEA1/IO108RSB1
K3	GEA0/IO107RSB1
K4	GEA2/IO106RSB1
K5	IO100RSB1
K6	IO98RSB1
K7	GND
K8	IO73RSB1
K9	GDC2/IO72RSB1
K10	GND
K11	GDA0/IO66RSB0
K12	GDB0/IO64RSB0
L1	GND
L2	VMV1
L3	GEB2/IO105RSB1
L4	IO102RSB1
L5	VCCIB1
L6	IO95RSB1
L7	IO85RSB1
L8	IO74RSB1
L9	TMS
L10	VJTAG
L11	VMV1
L12	TRST
M1	GNDQ
M2	GEC2/IO104RSB1
M3	IO103RSB1
M4	IO101RSB1
M5	IO97RSB1
M6	IO94RSB1
M7	IO86RSB1
M8	IO75RSB1
M9	TDI
M10	VCCIB1
M11	VPUMP
M12	GNDQ

FG256	
Pin Number	A3P400 Function
G13	GCC1/IO67PPB1
G14	IO64NPB1
G15	IO73PDB1
G16	IO73NDB1
H1	GFB0/IO146NPB3
H2	GFA0/IO145NDB3
H3	GFB1/IO146PPB3
H4	VCOMPLF
H5	GFC0/IO147NPB3
H6	VCC
H7	GND
H8	GND
H9	GND
H10	GND
H11	VCC
H12	GCC0/IO67NPB1
H13	GCB1/IO68PPB1
H14	GCA0/IO69NPB1
H15	NC
H16	GCB0/IO68NPB1
J1	GFA2/IO144PPB3
J2	GFA1/IO145PDB3
J3	VCCPLF
J4	IO143NDB3
J5	GFB2/IO143PDB3
J6	VCC
J7	GND
J8	GND
J9	GND
J10	GND
J11	VCC
J12	GCB2/IO71PPB1
J13	GCA1/IO69PPB1
J14	GCC2/IO72PPB1
J15	NC
J16	GCA2/IO70PDB1

FG256	
Pin Number	A3P400 Function
K1	GFC2/IO142PDB3
K2	IO144NPB3
K3	IO141PPB3
K4	IO120RSB2
K5	VCCIB3
K6	VCC
K7	GND
K8	GND
K9	GND
K10	GND
K11	VCC
K12	VCCIB1
K13	IO71NPB1
K14	IO74RSB1
K15	IO72NPB1
K16	IO70NDB1
L1	IO142NDB3
L2	IO141NPB3
L3	IO125RSB2
L4	IO139RSB3
L5	VCCIB3
L6	GND
L7	VCC
L8	VCC
L9	VCC
L10	VCC
L11	GND
L12	VCCIB1
L13	GDB0/IO78VPB1
L14	IO76VDB1
L15	IO76UDB1
L16	IO75PDB1
M1	IO140PDB3
M2	IO130RSB2
M3	IO138NPB3
M4	GEC0/IO137NPB3

FG256	
Pin Number	A3P400 Function
M5	VMV3
M6	VCCIB2
M7	VCCIB2
M8	IO108RSB2
M9	IO101RSB2
M10	VCCIB2
M11	VCCIB2
M12	VMV2
M13	IO83RSB2
M14	GDB1/IO78UPB1
M15	GDC1/IO77UDB1
M16	IO75NDB1
N1	IO140NDB3
N2	IO138PPB3
N3	GEC1/IO137PPB3
N4	IO131RSB2
N5	GNDQ
N6	GEA2/IO134RSB2
N7	IO117RSB2
N8	IO111RSB2
N9	IO99RSB2
N10	IO94RSB2
N11	IO87RSB2
N12	GNDQ
N13	IO93RSB2
N14	VJTAG
N15	GDC0/IO77VDB1
N16	GDA1/IO79UDB1
P1	GEB1/IO136PDB3
P2	GEB0/IO136NDB3
P3	VMV2
P4	IO129RSB2
P5	IO128RSB2
P6	IO122RSB2
P7	IO115RSB2
P8	IO110RSB2

FG484	
Pin Number	A3P600 Function
A1	GND
A2	GND
A3	VCCIB0
A4	NC
A5	NC
A6	IO09RSB0
A7	IO15RSB0
A8	NC
A9	NC
A10	IO22RSB0
A11	IO23RSB0
A12	IO29RSB0
A13	IO35RSB0
A14	NC
A15	NC
A16	IO46RSB0
A17	IO48RSB0
A18	NC
A19	NC
A20	VCCIB0
A21	GND
A22	GND
B1	GND
B2	VCCIB3
B3	NC
B4	NC
B5	NC
B6	IO08RSB0
B7	IO12RSB0
B8	NC
B9	NC
B10	IO17RSB0
B11	NC
B12	NC
B13	IO36RSB0
B14	NC

FG484	
Pin Number	A3P600 Function
B15	NC
B16	IO47RSB0
B17	IO49RSB0
B18	NC
B19	NC
B20	NC
B21	VCCIB1
B22	GND
C1	VCCIB3
C2	NC
C3	NC
C4	NC
C5	GND
C6	NC
C7	NC
C8	VCC
C9	VCC
C10	NC
C11	NC
C12	NC
C13	NC
C14	VCC
C15	VCC
C16	NC
C17	NC
C18	GND
C19	NC
C20	NC
C21	NC
C22	VCCIB1
D1	NC
D2	NC
D3	NC
D4	GND
D5	GAA0/IO00RSB0
D6	GAA1/IO01RSB0

FG484	
Pin Number	A3P600 Function
D7	GAB0/IO02RSB0
D8	IO11RSB0
D9	IO16RSB0
D10	IO18RSB0
D11	IO28RSB0
D12	IO34RSB0
D13	IO37RSB0
D14	IO41RSB0
D15	IO43RSB0
D16	GBB1/IO57RSB0
D17	GBA0/IO58RSB0
D18	GBA1/IO59RSB0
D19	GND
D20	NC
D21	NC
D22	NC
E1	NC
E2	NC
E3	GND
E4	GAB2/IO173PDB3
E5	GAA2/IO174PDB3
E6	GNDQ
E7	GAB1/IO03RSB0
E8	IO13RSB0
E9	IO14RSB0
E10	IO21RSB0
E11	IO27RSB0
E12	IO32RSB0
E13	IO38RSB0
E14	IO42RSB0
E15	GBC1/IO55RSB0
E16	GBB0/IO56RSB0
E17	IO52RSB0
E18	GBA2/IO60PDB1
E19	IO60NDB1
E20	GND

Revision	Changes	Page
Revision 10 (continued)	"TBD" for 3.3 V LVCMOS Wide Range in Table 2-28 • I/O Output Buffer Maximum Resistances1 through Table 2-30 • I/O Output Buffer Maximum Resistances1 was replaced by "Same as regular 3.3 V" (SAR 33852).	2-26 to 2-28
	The equations in the notes for Table 2-31 • I/O Weak Pull-Up/Pull-Down Resistances were corrected (SAR 32470).	2-28
	"TBD" for 3.3 V LVCMOS Wide Range in Table 2-32 • I/O Short Currents IOSH/IOSL through Table 2-34 • I/O Short Currents IOSH/IOSL was replaced by "Same as regular 3.3 V LVCMOS" (SAR 33852).	2-29 to 2-31
	In the "3.3 V LVCMOS Wide Range" section, values were added to Table 2-47 through Table 2-49 for IOSL and IOSH, replacing "TBD" (SAR 33852).	2-39 to 2-40
	The following sentence was deleted from the "2.5 V LVCMOS" section (SAR 24916): "It uses a 5 V–tolerant input buffer and push-pull output buffer."	2-47
	The table notes were revised for Table 2-90 • LVDS Minimum and Maximum DC Input and Output Levels (SAR 33859).	2-66
	Values were added for $F_{DDRIMAX}$ and F_{DDOMAX} in Table 2-102 • Input DDR Propagation Delays and Table 2-104 • Output DDR Propagation Delays (SAR 23919).	2-78, 2-80
	Table 2-115 • ProASIC3 CCC/PLL Specification was updated. A note was added to indicate that when the CCC/PLL core is generated by Microsemi core generator software, not all delay values of the specified delay increments are available (SAR 25705).	2-90
	The following figures were deleted (SAR 29991). Reference was made to a new application note, *Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs*, which covers these cases in detail (SAR 21770). Figure 2-34 • Write Access after Write onto Same Address Figure 2-35 • Read Access after Write onto Same Address Figure 2-35 • Read Access after Write onto Same Address The port names in the SRAM "Timing Waveforms", SRAM "Timing Characteristics" tables, Figure 2-39 • FIFO Reset, and the FIFO "Timing Characteristics" tables were revised to ensure consistency with the software names (SARs 29991, 30510).	2-92, 2-94, 2-99 2-102
	The "Pin Descriptions" chapter has been added (SAR 21642).	3-1
	Package names used in the "Package Pin Assignments" section were revised to match standards given in *Package Mechanical Drawings* (SAR 27395).	4-1
July 2010	The versioning system for datasheets has been changed. Datasheets are assigned a revision number that increments each time the datasheet is revised. The "ProASIC3 Device Status" table on page IV indicates the status for each device in the device family.	N/A

Revision	Changes	Page
Advance v0.6 (continued)	The "RESET" section was updated.	2-25
	The "WCLK and RCLK" section was updated.	2-25
	The "RESET" section was updated.	2-25
	The "RESET" section was updated.	2-27
	The "Introduction" of the "Advanced I/Os" section was updated.	2-28
	The "I/O Banks" section is new. This section explains the following types of I/Os: Advanced Standard+ Standard Table 2-12 • Automotive ProASIC3 Bank Types Definition and Differences is new. This table describes the standards listed above.	2-29
	PCI-X 3.3 V was added to the Compatible Standards for 3.3 V in Table 2-11 • VCCI Voltages and Compatible Standards	2-29
	Table 2-13 • ProASIC3 I/O Features was updated.	2-30
	The "Double Data Rate (DDR) Support" section was updated to include information concerning implementation of the feature.	2-32
	The "Electrostatic Discharge (ESD) Protection" section was updated to include testing information.	2-35
	Level 3 and 4 descriptions were updated in Table 2-43 • I/O Hot-Swap and 5 V Input Tolerance Capabilities in ProASIC3 Devices.	2-64
	The notes in Table 2-43 • I/O Hot-Swap and 5 V Input Tolerance Capabilities in ProASIC3 Devices were updated.	2-64
	The "Simultaneous Switching Outputs (SSOs) and Printed Circuit Board Layout" section is new.	2-41
	A footnote was added to Table 2-14 • Maximum I/O Frequency for Single-Ended and Differential I/Os in All Banks in Automotive ProASIC3 Devices (maximum drive strength and high slew selected).	2-30
	Table 2-18 • Automotive ProASIC3 I/O Attributes vs. I/O Standard Applications	2-45
	Table 2-50 • ProASIC3 Output Drive (OUT_DRIVE) for Standard I/O Bank Type (A3P030 device)	2-83
	Table 2-51 • ProASIC3 Output Drive for Standard+ I/O Bank Type was updated.	2-84
	Table 2-54 • ProASIC3 Output Drive for Advanced I/O Bank Type was updated.	2-84
	The "x" was updated in the "User I/O Naming Convention" section.	2-48
	The "VCC Core Supply Voltage" pin description was updated.	2-50
	The "VMVx I/O Supply Voltage (quiet)" pin description was updated to include information concerning leaving the pin unconnected.	2-50
	The "VJTAG JTAG Supply Voltage" pin description was updated.	2-50
	The "VPUMP Programming Supply Voltage" pin description was updated to include information on what happens when the pin is tied to ground.	2-50
	The "I/O User Input/Output" pin description was updated to include information on what happens when the pin is unused.	2-50
	The "JTAG Pins" section was updated to include information on what happens when the pin is unused.	2-51